

To our customers,

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April 1<sup>st</sup>, 2010  
Renesas Electronics Corporation

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## SWITCHING N-CHANNEL POWER MOS FET

**DESCRIPTION**

The 2SK3430 is N-channel MOS Field Effect Transistor designed for high current switching applications.

**FEATURES**

- Super low on-state resistance:  
 $R_{DS(on)1} = 7.3 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 40 \text{ A)}$   
 $R_{DS(on)2} = 15 \text{ m}\Omega \text{ MAX. (} V_{GS} = 4 \text{ V, } I_D = 40 \text{ A)}$
- Low  $C_{iss}$ :  $C_{iss} = 2800 \text{ pF TYP.}$
- Built-in gate protection diode

**ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25°C)**

|  |                |             |    |
|--|----------------|-------------|----|
| Drain to Source Voltage ( $V_{GS} = 0 \text{ V}$ )   | $V_{DSS}$      | 40          | V  |
| Gate to Source Voltage ( $V_{DS} = 0 \text{ V}$ )    | $V_{GSS}$      | $\pm 20$    | V  |
| Drain Current (DC) ( $T_C = 25^\circ\text{C}$ )      | $I_{D(DC)}$    | $\pm 80$    | A  |
| Drain Current (pulse) <sup>Note1</sup>               | $I_{D(pulse)}$ | $\pm 200$   | A  |
| Total Power Dissipation ( $T_C = 25^\circ\text{C}$ ) | $P_T$          | 84          | W  |
| Total Power Dissipation ( $T_A = 25^\circ\text{C}$ ) | $P_T$          | 1.5         | W  |
| Channel Temperature                                  | $T_{ch}$       | 150         | °C |
| Storage Temperature                                  | $T_{stg}$      | -55 to +150 | °C |
| Single Avalanche Current <sup>Note2</sup>            | $I_{AS}$       | 37          | A  |
| Single Avalanche Energy <sup>Note2</sup>             | $E_{AS}$       | 137         | mJ |

**Notes 1.**  $PW \leq 10 \mu\text{s}$ , Duty cycle  $\leq 1\%$

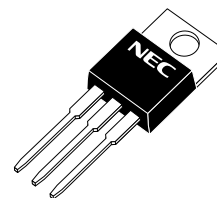
**2.** Starting  $T_{ch} = 25^\circ\text{C}$ ,  $V_{DD} = 20 \text{ V}$ ,  $R_G = 25 \Omega$ ,  $V_{GS} = 20 \rightarrow 0 \text{ V}$

**ORDERING INFORMATION**

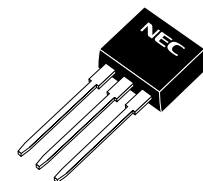
| PART NUMBER | PACKAGE                   |
|-------------|---------------------------|
| 2SK3430     | TO-220AB                  |
| 2SK3430-S   | TO-262                    |
| 2SK3430-ZJ  | TO-263                    |
| 2SK3430-Z   | TO-220SMD <sup>Note</sup> |

**Note** TO-220SMD package is produced only in Japan.

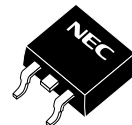
(TO-220AB)



(TO-262)



(TO-263, TO-220SMD)

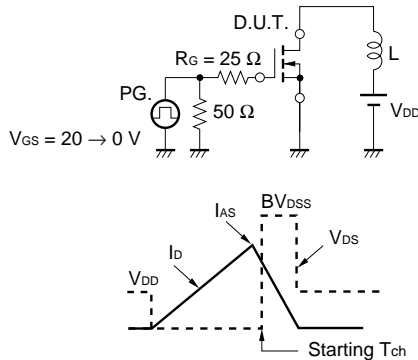


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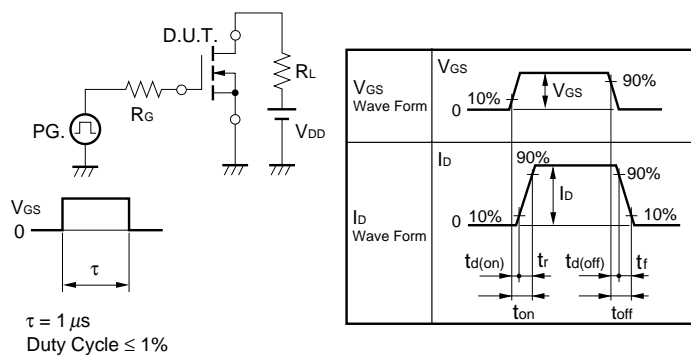
**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C)**

| CHARACTERISTICS                     | SYMBOL               | TEST CONDITIONS                               | MIN. | TYP. | MAX. | UNIT |
|-------------------------------------|----------------------|---|------|------|------|------|
| Zero Gate Voltage Drain Current     | I <sub>DSS</sub>     | V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V |      |      | 10   | μA   |
| Gate Leakage Current                | I <sub>GSS</sub>     | V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0V |      |      | ±10  | μA   |
| Gate Cut-off Voltage                | V <sub>GS(off)</sub> | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA | 1.5  | 2.0  | 2.5  | V    |
| Forward Transfer Admittance         | y <sub>fs</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 40 A | 20   | 40   |      | S    |
| Drain to Source On-state Resistance | R <sub>DS(on)1</sub> | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 40 A |      | 5.9  | 7.3  | mΩ   |
|                                     | R <sub>DS(on)2</sub> | V <sub>GS</sub> = 4 V, I <sub>D</sub> = 40 A  |      | 10.5 | 15   | mΩ   |
| Input Capacitance                   | C <sub>iss</sub>     | V <sub>DS</sub> = 10 V,                       |      | 2800 |      | pF   |
| Output Capacitance                  | C <sub>oss</sub>     | V <sub>GS</sub> = 0 V,                        |      | 730  |      | pF   |
| Reverse Transfer Capacitance        | C <sub>rss</sub>     | f = 1 MHz                                     |      | 320  |      | pF   |
| Turn-on Delay Time                  | t <sub>d(on)</sub>   | V <sub>DD</sub> = 20 V, I <sub>D</sub> = 40 A |      | 110  |      | ns   |
| Rise Time                           | t <sub>r</sub>       | V <sub>GS</sub> = 10 V                        |      | 1800 |      | ns   |
| Turn-off Delay Time                 | t <sub>d(off)</sub>  | R <sub>G</sub> = 10 Ω                         |      | 170  |      | ns   |
| Fall Time                           | t <sub>f</sub>       |   |      | 350  |      | ns   |
| Total Gate Charge                   | Q <sub>G</sub>       | V <sub>DD</sub> = 32 V                        |      | 50   |      | nC   |
| Gate to Source Charge               | Q <sub>GS</sub>      | V <sub>GS</sub> = 10 V                        |      | 10   |      | nC   |
| Gate to Drain Charge                | Q <sub>GD</sub>      | I <sub>D</sub> = 80 A                         |      | 14   |      | nC   |
| Body Diode Forward Voltage          | V <sub>F(S-D)</sub>  | I <sub>F</sub> = 80 A, V <sub>GS</sub> = 0 V  |      | 1.0  |      | V    |
| Reverse Recovery Time               | t <sub>rr</sub>      | I <sub>F</sub> = 80 A, V <sub>GS</sub> = 0 V  |      | 50   |      | ns   |
| Reverse Recovery Charge             | Q <sub>rr</sub>      | di/dt = 100 A/μs                              |      | 77   |      | nC   |

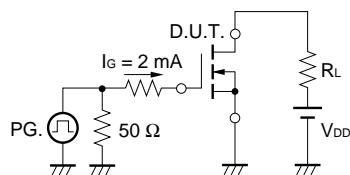
**TEST CIRCUIT 1 AVALANCHE CAPABILITY**



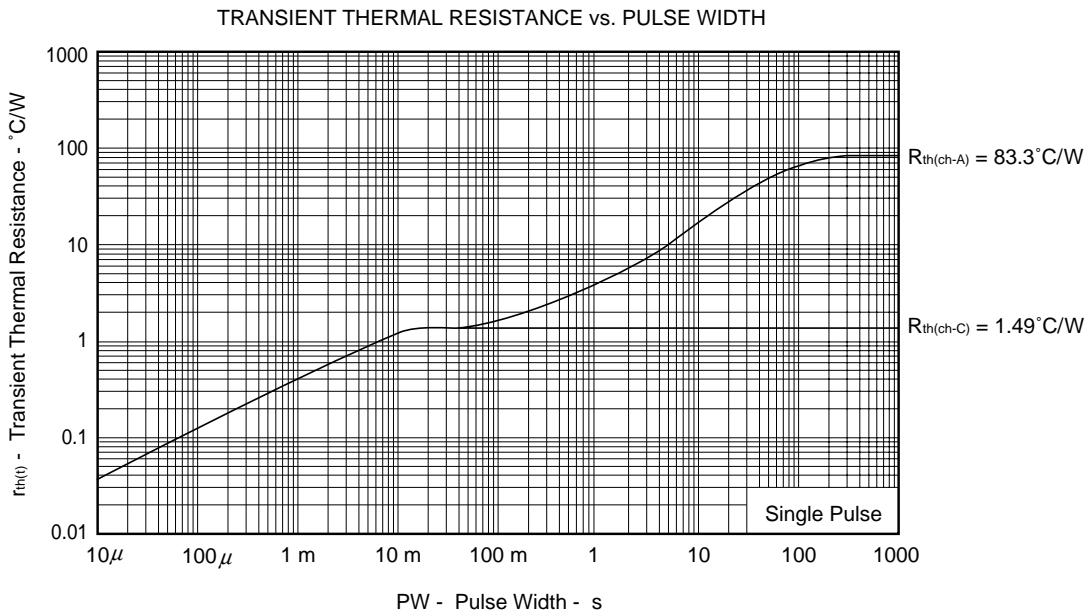
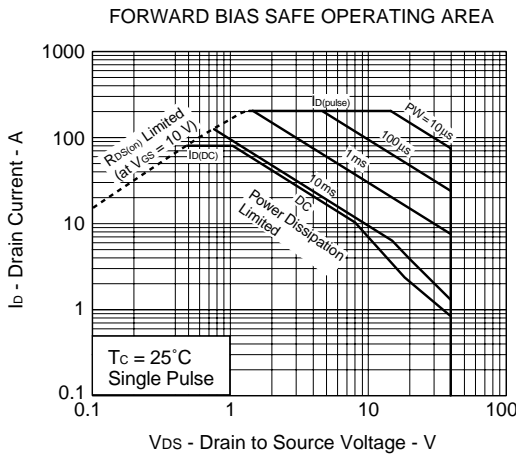
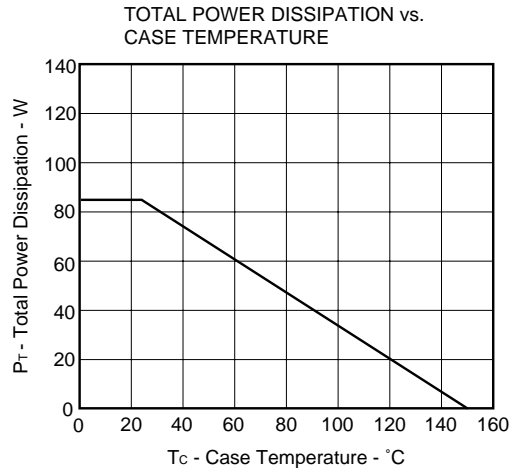
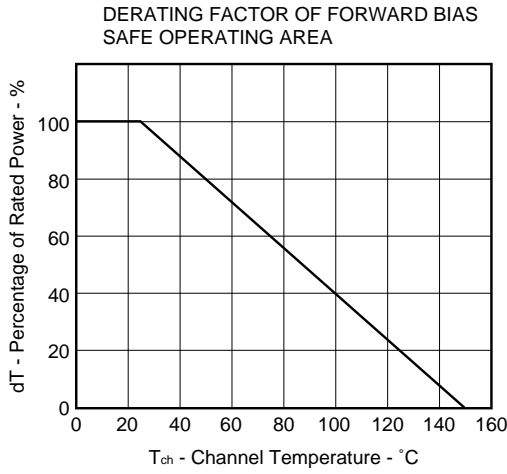
**TEST CIRCUIT 2 SWITCHING TIME**



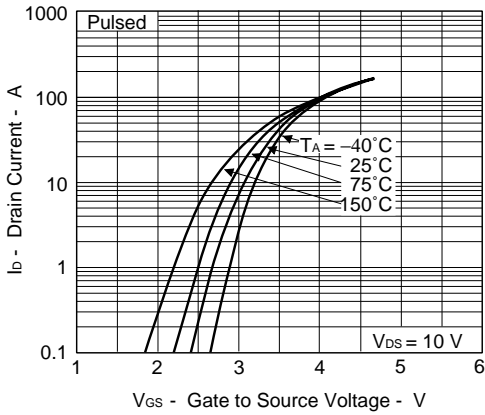
**TEST CIRCUIT 3 GATE CHARGE**



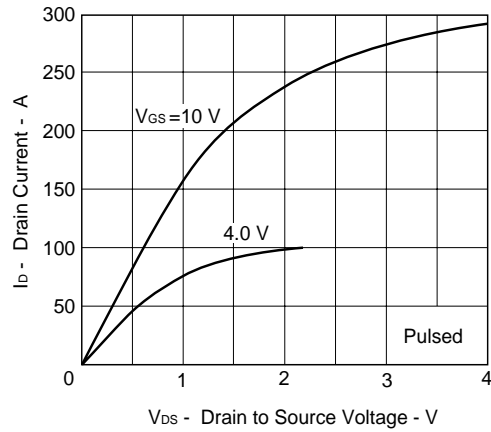
TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C)



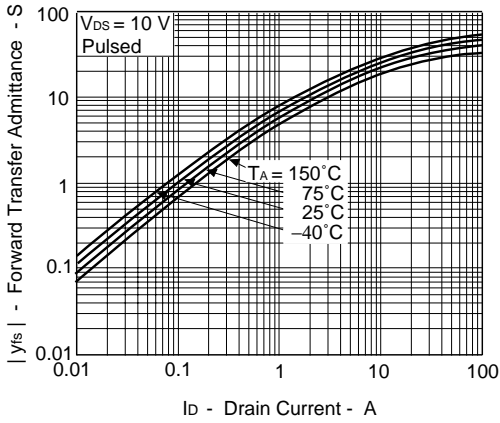
FORWARD TRANSFER CHARACTERISTICS



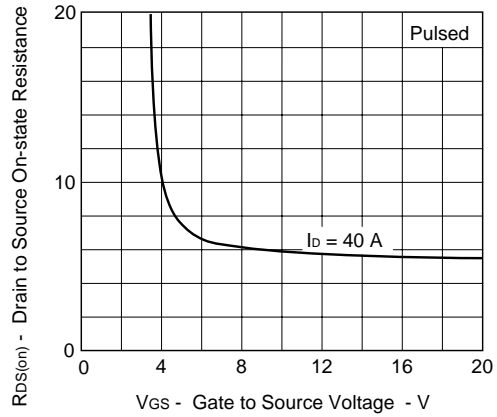
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



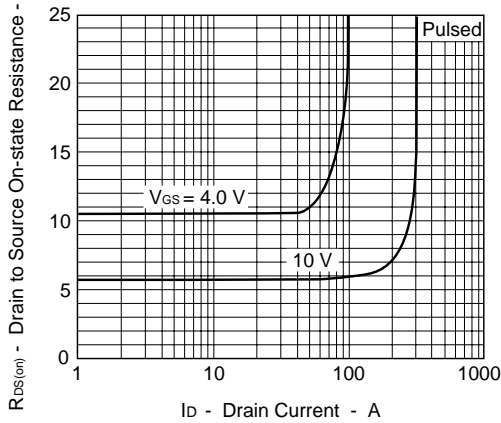
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



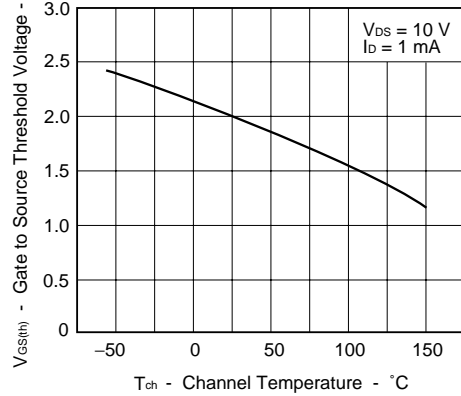
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



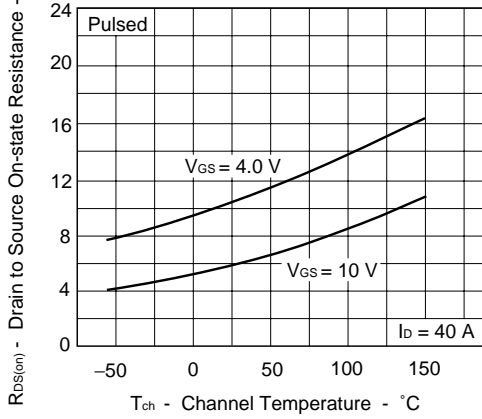
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



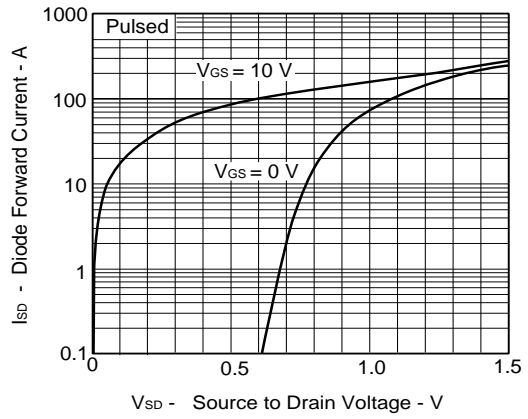
GATE TO SOURCE THRESHOLD VOLTAGE vs. CHANNEL TEMPERATURE



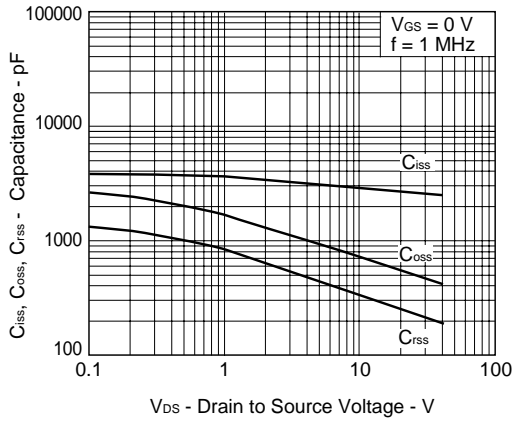
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



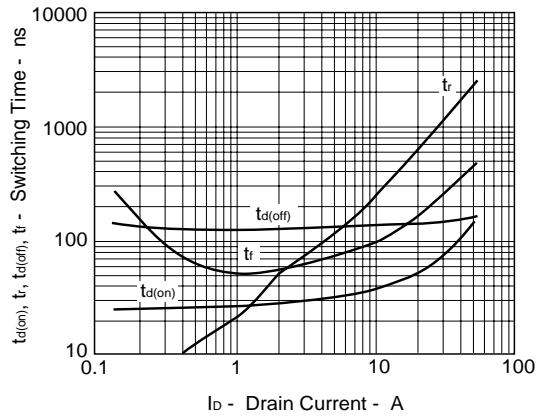
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



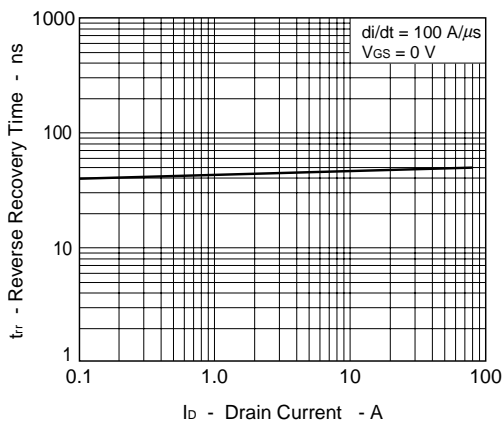
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



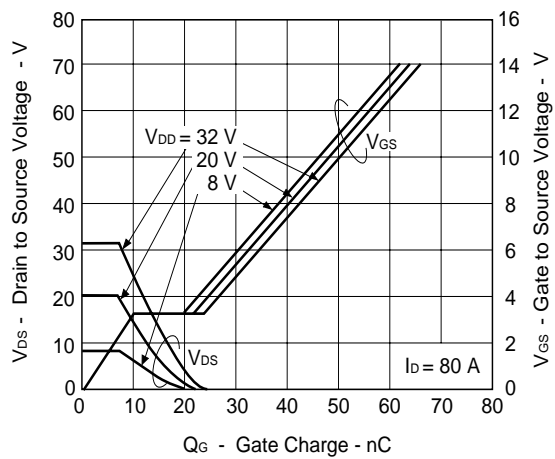
SWITCHING CHARACTERISTICS

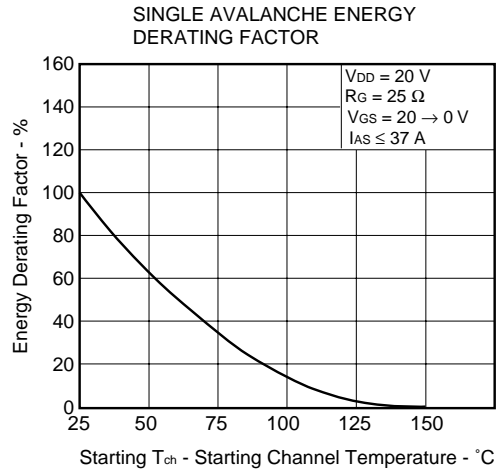
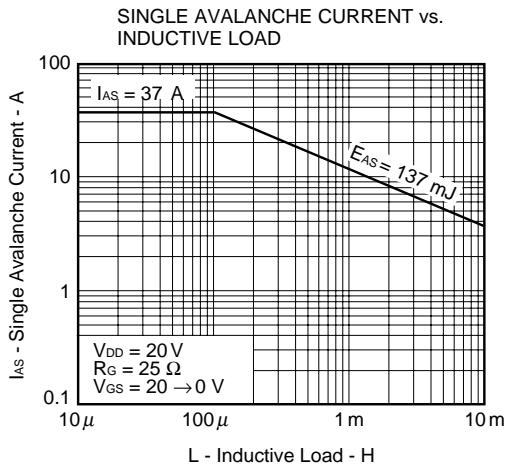


REVERSE RECOVERY TIME vs. DRAIN CURRENT



DYNAMIC INPUT/OUTPUT CHARACTERISTICS

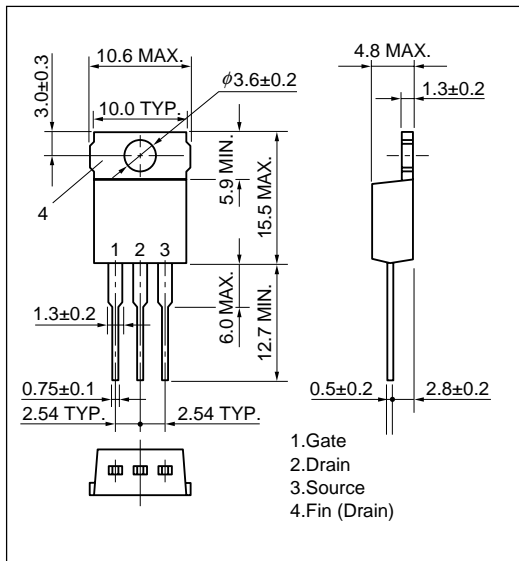




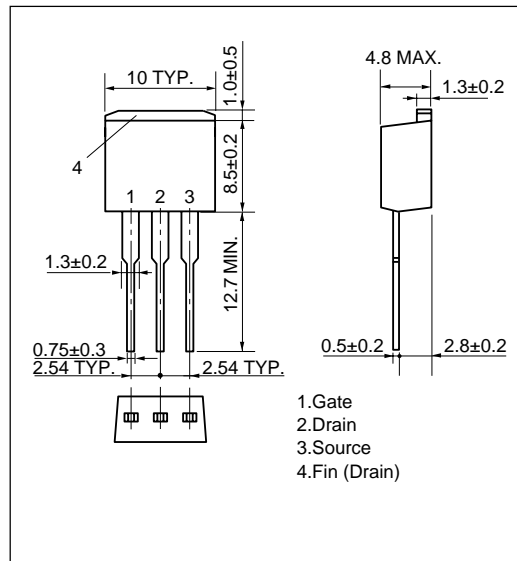


★ PACKAGE DRAWINGS (Unit: mm)

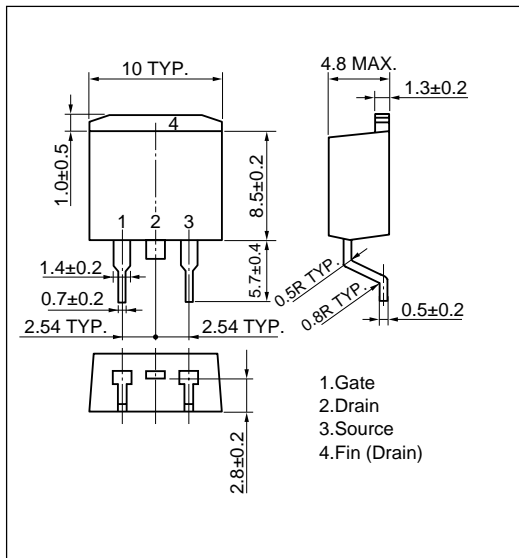
1) TO-220AB(MP-25)



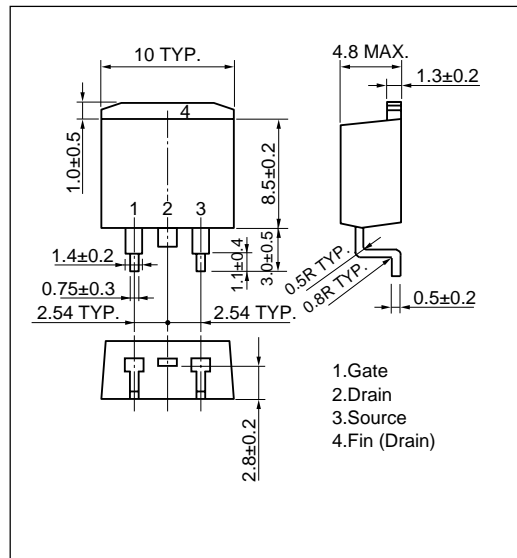
2) TO-262(MP-25 Fin Cut)



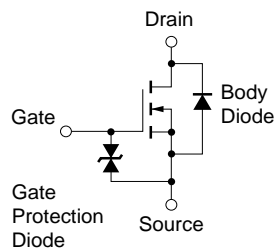
3) TO-263 (MP-25ZJ)



4) TO-220SMD (MP-25Z)<sup>Note</sup>



EQUIVALENT CIRCUIT



**Note** This package is produced only in Japan.

**Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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